



Low Voltage Detectors (VDF= 0.8V~1.5V) Standard Voltage Detectors (VDF= 1.6V~6.0V)

#### CMOS

Highly Accurate	: ±2%
Low Power Consumption	: 0.7 µ A
	(VIN = 1.5V)
Ultra Small Package	: USP-3

#### **GENERAL DESCRIPTION**

The XC61G series are highly precise, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies.

Detect voltage is extremely accurate with minimal temperature drift.

Both CMOS and N-channel open drain output configurations are available.

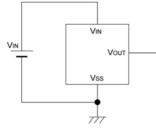
#### APPLICATIONS

Microprocessor reset circuitry Memory battery back-up circuits Power-on reset circuits Power failure detection System battery life and charge voltage monitors

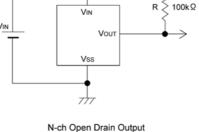
#### **FEATURES**

Highly Accurate	± 2%
Low Power Consumption	: 0.7 μA[VIN=1.5V](TYP.)
Detect Voltage Range	: 0.8V ~ 1.5V in 100mV
	increments(Low Voltage)
	: 1.6V ~ 6.0V in 100mV
	increments(Standard Voltage)
Operating Voltage Range	: 0.7V ~ 6.0V(Low Voltage)
	: 0.7V ~ 10.0V(Standard Voltage)
Detect Voltage Temperate	ure characteristics
	: ± 100ppm/ (TYP.)
Output Configuration	: N-channel open drain or CMOS
Ultra Small Package	: USP-3(120mW)

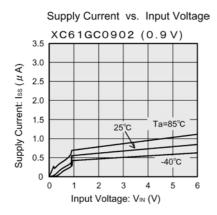
#### **TYPICAL APPLICATION CIRCUITS**

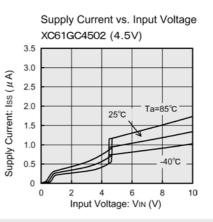




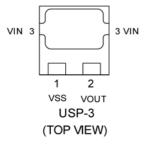


## TYPICAL PERFORMANCE CHARACTERISTICS





## **PIN CONFIGURATION**



### **PIN ASSIGNMENT**

PIN NUMBER	PIN NAME	FUNCTION	
USP-3		FUNCTION	
3	Vin	Supply Voltage	
1	Vss	Ground	
2	Vout	Output	

# PRODUCT CLASSIFICATION

Ordering Information

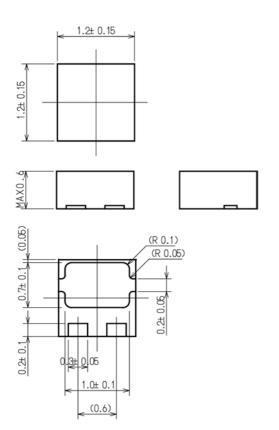
<u>XC61G</u>

DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION
	Output Configuration	С	: CMOS output
	Output Configuration	N	: N-ch open drain output
	Detect Voltage	08 ~ 60	: e.g. 0.9V 0, 9
			: e.g. 1.5V 1, 5
	Output Delay	0	: No delay
	Detect Accuracy	2	: Within ± 2%
	Package	Н	: USP-3
	Device Orientation	R	: Embossed tape, Standard feed
	Device Orientation	L	: Embossed tape, Reverse feed

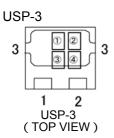
XC61G Series

# PACKAGING INFORMATION

USP-3



#### MARKING RULE



Represents integer of output voltage and detect voltage

CMOS	Output	(XC61GC	series)
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MARK	CONFIGURATION	VOLTAGE(V)
А	CMOS	0.X
В	CMOS	1.X

N-Channel Open Drain Ou	utput (XC61GN series)
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DESIGNATOR	CONFIGURATION	VOLTAGE(V)
К	N-ch	0.X
L	N-ch	1.X

Represents decimal number of detect voltage

MARK	VOLTAGE (V)	DESIGNATOR	VOLTAGE (V)
0	X.0	5	X.5
1	X.1	6	X.6
2	X.2	7	X.7
3	X.3	8	X.8
4	X.4	9	X.9

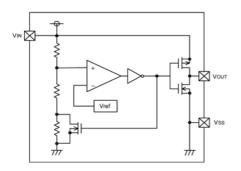
Based on internal standards (SSOT-24 excepted)

MARK	
3	

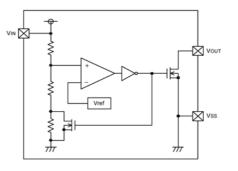
Represents production lot number 0 to 9, A to Z repeated (G,I,J,O,Q,W excepted)

#### **BLOCK DIAGRAMS**

(1)CMOS Output



(2)N-ch Open Drain Output



# ABSOLUTE MAXIMUM RATINGS

F	PARAMETER		SYMBOL	RATINGS	UNITS
Input Voltage *1		Vin	9.0	V	
input ve	Jilage	*2	VIN	12.0	v
Output C	urrent	*1	Іоит	50	mA
Output C	unent	*2	1001	50	IIIA
	CMOS			Vss -0.3 ~ Vin +0.3	
Output Voltage	N-ch Open Dra	ain Output *1	Vout	Vss -0.3 ~ 9.0	V
	N-ch Open Dra	ain Output *2		Vss -0.3 ~ 12.0	
Power	USP	2	Pd	120	mW
Dissipation	USF-3		Fu	120	IIIVV
Operating Temperature Range		Topr	-40 ~ +85		
Strage Temperature Range		Tstg	-40 ~ +125		

\*1 Low voltage

\*2 Standard voltage

# ELECTRICAL CHARACTERISTICS

VDF (T) = 0.9 to 1.5V  $\pm$  2%

$VDF(1) = 0.9 \text{ to } 1.5V \pm 2\%$								Ta=25
PARAMETER	SYMBOL	CONDITIO	MIN.	TYP.	MAX.	UNITS	CIRCUITS	
Detect Voltage	Vdf			Vdf x 0.98	Vdf	VDF x 1.02	V	1
Hysteresis Range	VHYS			VDF x 0.02	VDF x 0.05	Vdf x 0.08	V	1
		VIN = 1.5	ΰV	-	0.7	2.3		
		= 2.0	V	-	0.8	2.7		
Supply Current	Iss	= 3.0	V	-	0.9	3.0	μA	2
		= 4.0	V	-	1.0	3.2		
		= 5.0	V	-	1.1	3.6		
Operating Voltage	Vin	VDF(T) = 0.9V t		0.7	-	6.0	- V	1
	VIIN	VDF(T) = 1.6V t	o 6.0V	0.7	-	10.0		
Output Current		N-ch, VDS = 0.5V	VIN =0.7V	0.10	0.80	-		3
Output Current (Low Voltage)			VIN =1.0V	0.85	2.70	-		5
(LOW Voltage)		CMOS, P-ch, VDS=2.1	/ VIN =6.0V	-	-7.5	-1.5		4
			VIN =1.0V	1.0	2.2	-		
	Ιουτ	N-ch, VDS = 0.5V	VIN =2.0V	3.0	7.7	-	mA	3
Output Current			VIN =3.0V	5.0	10.1	-		
(Standard Voltage)			VIN =4.0V	6.0	11.5	-		
			VIN =5.0V	7.0	13.0	-		
		CMOS, P-ch, VDS=2.1V VIN =8.0V		-	-10.0	-2.0		4
Temperature Characteristics	VDF Topr• VDF	-40 Topr	85	-	± 100	-	ppm/	-
Delay Time (VDR VOUT inversion)	tDLY			-	-	0.2	ms	5

NOTE : VDF (T) : Setting detect voltage Release Voltage : VDR = VDF + VHYS

#### **OPERATIONAL EXPLANATION**

#### CMOS output

When input voltage (VIN) rises above detect voltage (VDF), output voltage (VOUT) will be equal to VIN.

( A condition of high impedance exists with N-ch open drain output configurations. )

When input voltage (VIN) falls below detect voltage (VDF), output voltage (VOUT) will be equal to the ground voltage (Vss) level.

When input voltage (VIN) falls to a level below that of the minimum operating voltage (VMIN), output will become unstable. In this condition, VIN will equal the pulled-up output ( should output be pulled-up.)

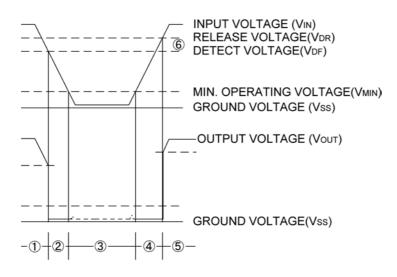
When input voltage (VIN) rises above the ground voltage (Vss) level, output will be unstable at levels below the minimum operating voltage (VMIN). Between the VMIN and detect release voltage (VDR) levels, the ground voltage (Vss) level will be maintained.

When input voltage (VIN) rises above detect release voltage (VDR), output voltage (VOUT) will be equal to VIN.

( A condition of high impedance exists with N-ch open drain output configurations. )

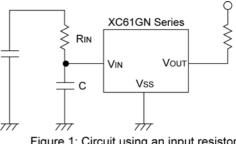
The difference between VDR and VDF represents the hysteresis range.

#### **Timing Chart**



### NOTES ON USE

- 1. Please use this IC within the stated maximum ratings. Operation beyond these limits may cause degrading or permanent damage to the device.
- When a resistor is connected between the VIN pin and the input with CMOS output configurations, oscillation may occur 2. as a result of voltage drops at RIN if load current (IOUT) exists. (refer to the Oscillation Description (1) below)
- 3. When a resistor is connected between the VIN pin and the input with CMOS output configurations, irrespective of N-ch output configurations, oscillation may occur as a result of through current at the time of voltage release even if load current (IOUT) does not exist. (refer to the Oscillation Description (2) below)
- 4. With a resistor connected between the VIN pin and the input, detect and release voltage will rise as a result of the IC's supply current flowing through the VIN pin.
- 5. In order to stabilise the IC's operations, please ensure that VIN pin's input frequency's rise and fall times are more than several µ sec / V.
- 6. Please use N-ch open drains configuration, when a resistor RIN is connected between the VIN pin and power source. In such cases, please ensure that RIN is less than  $10k\Omega$  and that C is more than  $0.1\mu$ F.



#### Figure 1: Circuit using an input resistor

**A** TOREX

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#### **Oscillation Description**

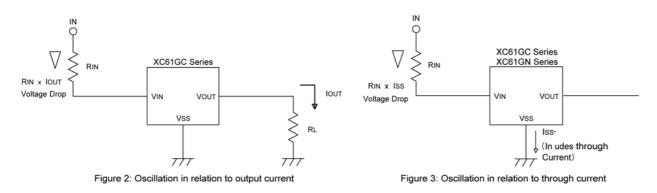
(1) Output current oscillation with the CMOS output configuration

When the voltage applied at IN rises, release operations commence and the detector's output voltage increases. Load current (IOUT) will flow at RL. Because a voltage drop (RIN x IOUT) is produced at the RIN resistor, located between the input (IN) and the VIN pin, the load current will flow via the IC's VIN pin. The voltage drop will also lead to a fall in the voltage level at the VIN pin. When the VIN pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at RIN will disappear, the voltage level at the VIN pin will rise and release operations will begin over again.

Oscillation may occur with this " release - detect - release " repetition.

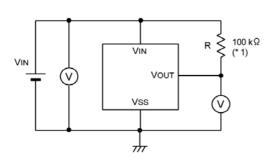
Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current Since the XC61G series are CMOS IC s, through current will flow when the IC's internal circuit switching operates (during release and detect operations ). Consequently, oscillation is liable to occur as a result of drops in voltage at the through current's resistor (RIN) during release voltage operations. (refer to Figure 3) Since hysteresis exists during detect operations, oscillation is unlikely to occur.

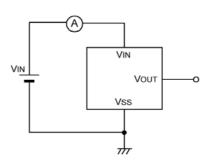


#### **TEST CIRCUITS**

Circuit 1

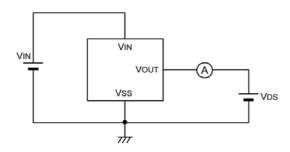


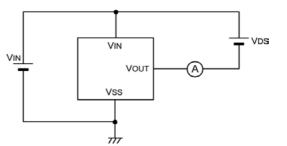




Circuit 3

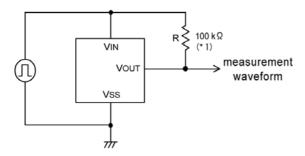
Circuit 4





h

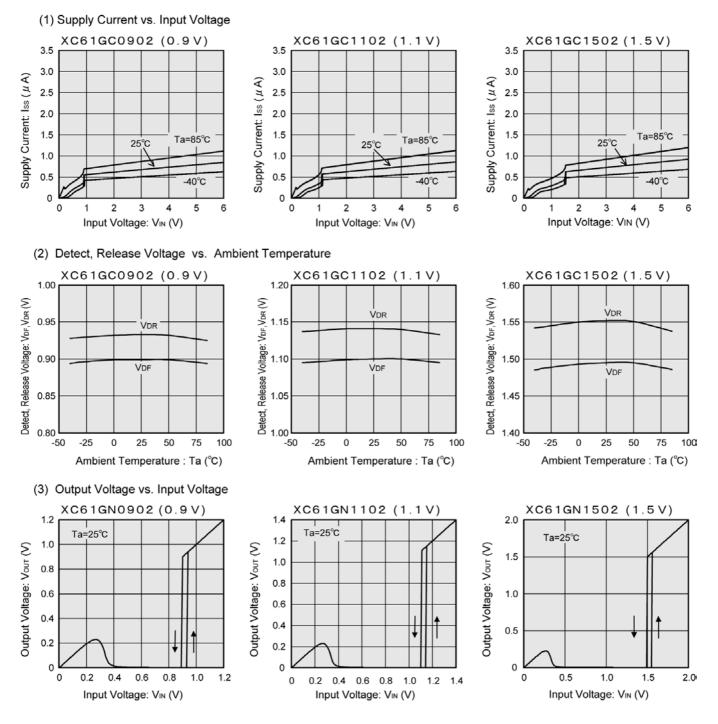
Circuit 5



\* 1 : The resistor is not necessary with CMOS output products.

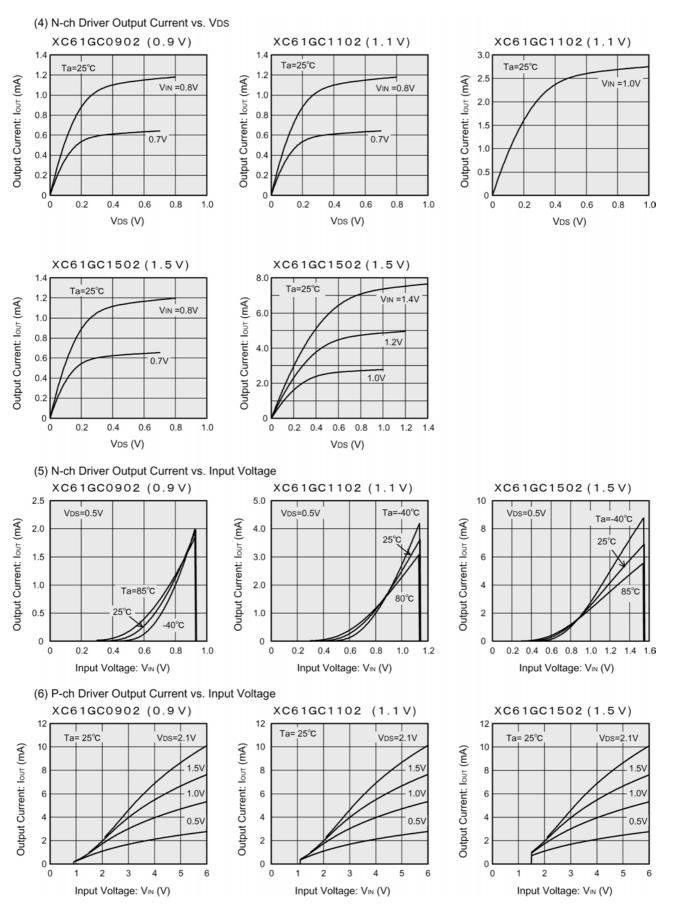
#### TYPICAL PERFORMANCE CHARACTERISTICS

#### Low Voltage

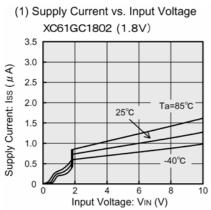


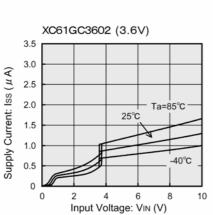
Note : Unless otherwise stated, the N-channel open drain pull-up resistance value is  $100 k \Omega$ .

Low Voltage (Continued)

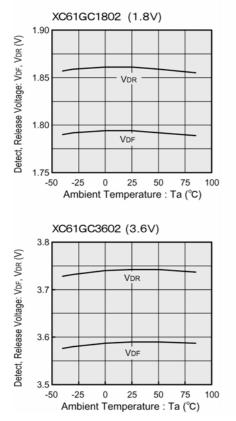


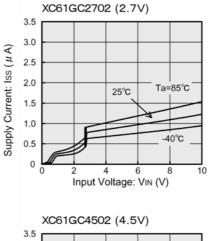
#### Standard Voltage

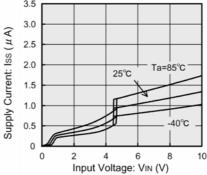


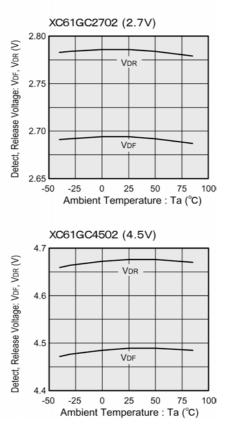






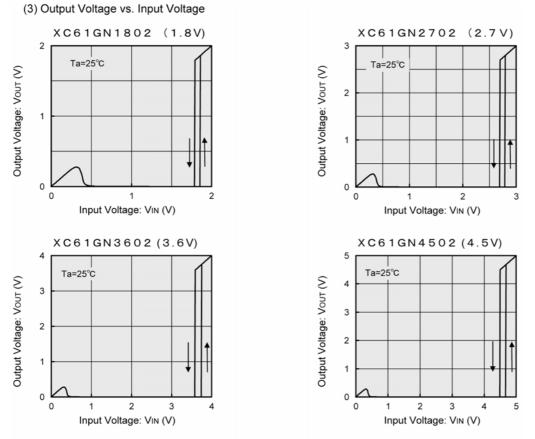




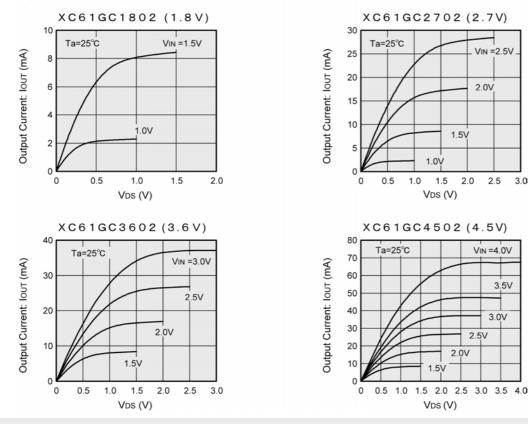


TOREX 111

Standard Voltage (Continued)



#### Note : The N-channel open drain pull up resistance value is $100 k \Omega$ .

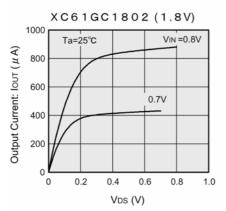


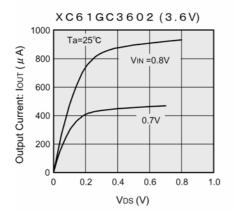
3.0

(4) N-ch Driver Output Current vs. VDs

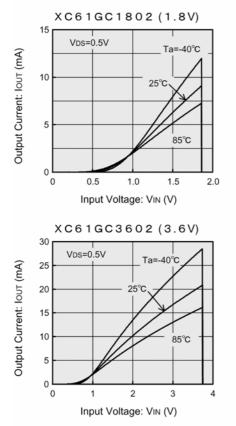
#### Standard Voltage (Continued)

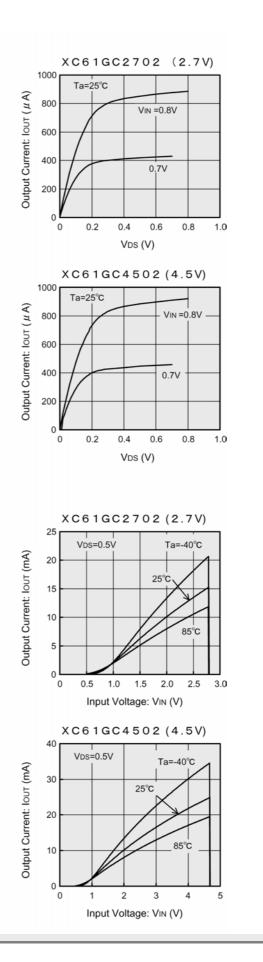






(5) N-ch Driver Output Current vs. Input Voltage





TOREX 113

#### Standard Voltage (Continued)

(6) P-ch Driver Output Current vs. Input Voltage

